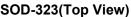


Description

The PESDNC3D5VBL protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.





Feature

- > 80W peak pulse power per line ($t_P = 8/20\mu s$)
- SOD-323 package
- Bidirectional configurations
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30kV(air), ± 30kV(contact); IEC 61000-4-5 (Lightning) 8A (8/20us)

Applications

- Laptop computers
- Cellular phones
- Digital cameras
- PDAs

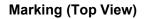
Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Pure tin plating: 7 ~ 17 um









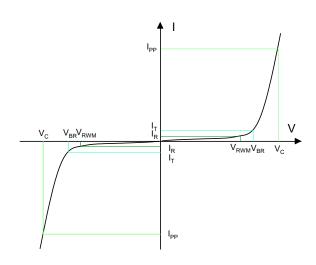
PESDNC3D5VBL

ESD Protector

PESDNC3D5VBL

Electronics Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V _{BR}	Breakdown Voltage @ I _T		
Ι _Τ	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _c	Clamping Voltage @ I _{PP}		
P _{PP}	P _{PP} Peak Pulse Power		
CJ	C _J Junction Capacitance		
I _F	I _F Forward Current		
V _F	V _F Forward Voltage @ I _F		



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}	-	-	-	5.0	V
Breakdown Voltage	V _{BR}	I _t = 1mA	5.6	-	7.5	V
Reverse Leakage Current	I _R	V _{RWM} = 5V	-	-	1.0	μA
Clamping Voltage ¹⁾	V _c	TLP = 16A, t _p = 100ns	-	9.2	-	V
Dynamic resistance ¹⁾	R_{DYN}	-	-	0.25	-	Ω
Clemning Voltage ²	V _c	I _{PP} = 1A,t _P = 8/20μs	-	7.5	9.0	V
Clamping Voltage ²⁾		I _{PP} = 8A,t _P = 8/20μs	-	9.0	11.0	V
Junction Capacitance	CJ	V _R = 0V,f = 1MHz	-	18.0	25.0	pF

Notes:

1. TLP parameter: Z_0 =50 Ω , t_p =100ns, t_r =2ns, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

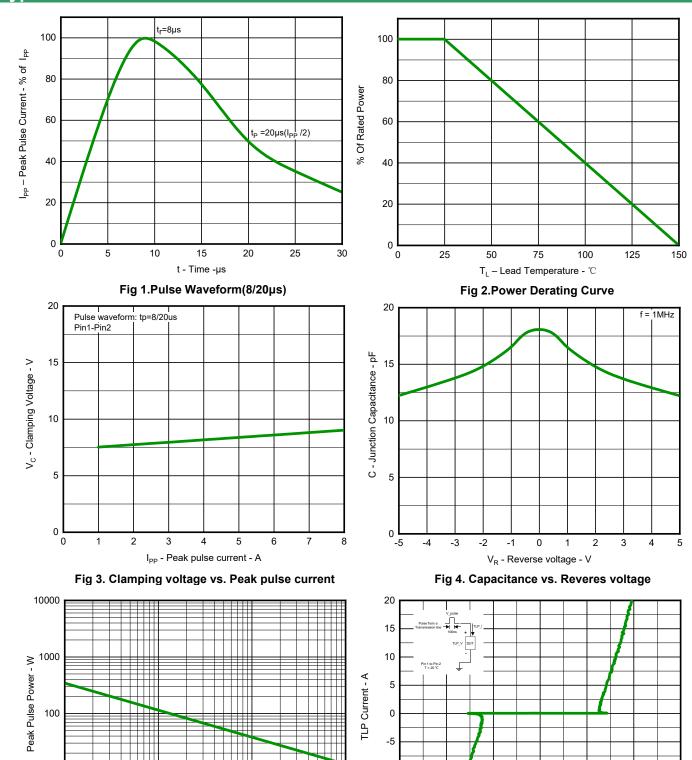
2. Non-repetitive current pulse, according to IEC61000-4-5.

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20µs)	P _{PP}	80	W
Peak Pulse Current (t _P = 8/20µs)	I _{PP}	8	А
Lead Soldering Temperature	Τ _L	260 (10 sec)	°C
Junction and Storage Temperature Range	T _{J,} T _{STG}	-55~+150	°C
ESD Protection-Contact Discharge	V _{ESD}	±30	kV
ESD Protection-Air Discharge	V _{ESD}	±30	kV

PESDNC3D5VBL

Typical Characteristics



10

10

Pulse Duration - µs Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

100

15

10

5

1000

-5

-10

-15

-20

-15

-10

-5

0

TLP Voltage - V

Fig 6. TLP Measurement

PESDNC3D5VBL

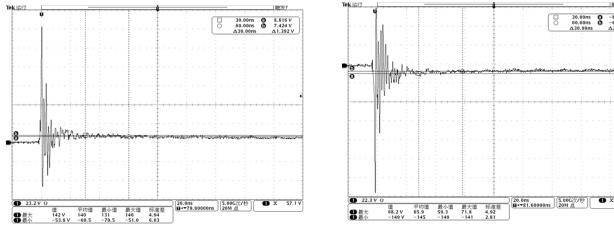
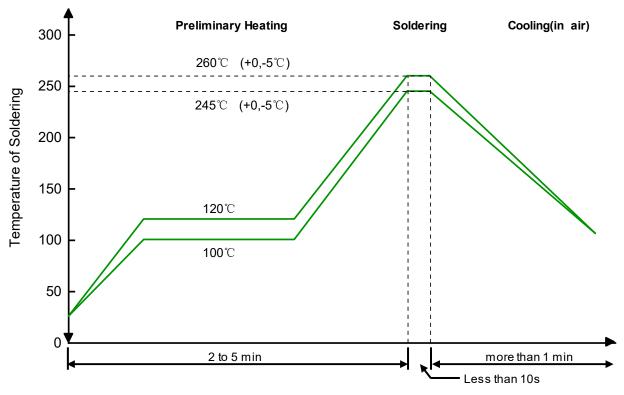


Fig 7. Clamping Voltage at IEC61000-4-2 +8kV Pulse Waveform

Fig 8. Clamping Voltage at IEC61000-4-2 -8kV Pulse Waveform

Solder Reflow Recommendation



Remark: Pb free for 260°C; Pb for 245°C.

PESDNC3D5VBL

ESD Protector

PCB Design

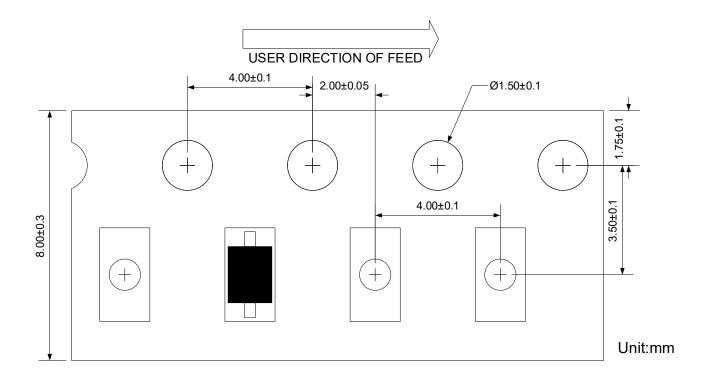
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- > Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

Ordering information

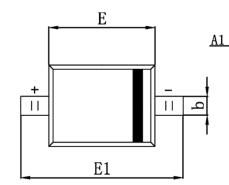
Device Package		Reel	Shipping	
PESDNC3D5VBL	SOD-323 (Pb-Free)	7"	3000 / Tape & Reel	

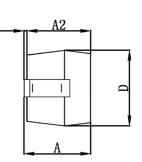
Load with information

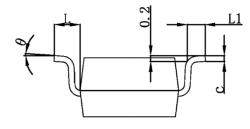


PESDNC3D5VBL

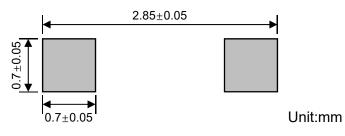
Product dimension (SOD-323)







Dim	Millim	neters	Inches		
Dilli	Min	Max	Min	Max	
А	0.800	1.000	0.031	0.039	
A1	0.000	0.100	0.000	0.004	
A2	0.800	0.900	0.031	0.035	
b	0.250	0.350	0.010	0.014	
с	0.080	0.150	0.003	0.006	
D	1.200	1.400	0.047	0.055	
Е	1.600	1.800	0.063	0.071	
E1	2.550	2.750	0.100	0.108	
L	0.475 Ref.		0.019 Ref.		
L1	0.250	0.400	0.010	0.016	
θ	0°	8°	0°	8°	



Suggested PCB Layout

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